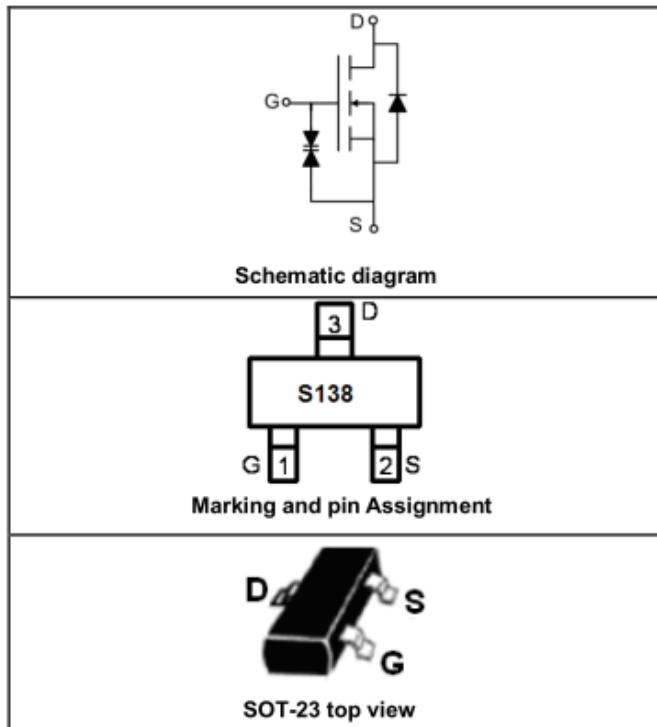


GENERAL FEATURES

- $V_{DS} = 50V, I_D = 0.22A$
- $R_{DS(ON)} < 6\Omega @ V_{GS}=4.5V$
- $R_{DS(ON)} < 3.5\Omega @ V_{GS}=10V$
- ESD Rating : 1000V HBM
- High Power and current handling capability
- Halogen Free product is acquired
- Surface Mount Package

Applications

- Direct Logic-Level Interface: TTL/CMOS
- Drivers: Relays, Solenoids, Lamps, Hammers, Display, Memories, Transistors, etc.
- Battery Operated Systems
- Solid-State Relays



PACKAGE MARKING AND ORDERING INFORMATION

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
S138	BSS138-HF	SOT-23	Ø180mm	8 mm	3000 units

ABSOLUTE MAXIMUM RATINGS($T_A=25^\circ C$ unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DS}	50	V
Gate-Source Voltage	V_{GS}	± 20	V
Drain Current-Continuous@ Current-Pulsed (Note 1)	I_D	0.22	A
	$I_D(70^\circ C)$	0.18	
	I_{DM}	0.88	A
Maximum Power Dissipation	P_D	0.43	W
Operating Junction and Storage Temperature Range	T_J, T_{STG}	-55 To 175	°C

THERMAL CHARACTERISTICS

Parameter	Symbol	Limit	Unit
Thermal Resistance,Junction-to-Ambient (Note 2)	$R_{\theta JA}$	350	°C/W



N-Channel MOS

BSS138

ELECTRICAL CHARACTERISTICS ($T_A=25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
OFF CHARACTERISTICS						
Drain-Source Breakdown Voltage	BV_{DSS}	$\text{V}_{\text{GS}}=0\text{V}, \text{I}_{\text{D}}=250\mu\text{A}$	50			V
Zero Gate Voltage Drain Current	I_{DSS}	$\text{V}_{\text{DS}}=50\text{V}, \text{V}_{\text{GS}}=0\text{V}$			1	μA
Gate-Body Leakage Current	I_{GSS}	$\text{V}_{\text{GS}}=\pm 20\text{V}, \text{V}_{\text{DS}}=0\text{V}$			10	uA
Gate-Source Breakdown Voltage	BV_{GSO}	$\text{V}_{\text{DS}}=0\text{V}, \text{I}_{\text{G}}=\pm 250\mu\text{A}$	± 20			V
ON CHARACTERISTICS (Note 3)						
Gate Threshold Voltage	$\text{V}_{\text{GS(th)}}$	$\text{V}_{\text{DS}}=\text{V}_{\text{GS}}, \text{I}_{\text{D}}=250\mu\text{A}$	0.8		1.5	V
Drain-Source On-State Resistance	$\text{R}_{\text{DS(ON)}}$	$\text{V}_{\text{GS}}=10\text{V}, \text{I}_{\text{D}}=0.22\text{A}$			3.5	Ω
		$\text{V}_{\text{GS}}=4.5\text{V}, \text{I}_{\text{D}}=0.22\text{A}$			6	
Forward Transconductance	g_{FS}	$\text{V}_{\text{DS}}=10\text{V}, \text{I}_{\text{D}}=0.22\text{A}$		0.1		S
DYNAMIC CHARACTERISTICS (Note 4)						
Input Capacitance	C_{iss}	$\text{V}_{\text{DS}}=25\text{V}, \text{V}_{\text{GS}}=0\text{V}, \text{F}=1.0\text{MHz}$		30		PF
Output Capacitance	C_{oss}			15		
Reverse Transfer Capacitance	C_{rss}			6		
SWITCHING CHARACTERISTICS (Note 4)						
Turn-on Delay Time	$\text{t}_{\text{d(on)}}$	$\text{V}_{\text{DD}}=30\text{V}, \text{V}_{\text{GS}}=10\text{V}, \text{R}_{\text{GEN}}=6\Omega, \text{I}_{\text{D}}=0.22\text{A}$		2.6		nS
Turn-On Rise Time	t_r			9		
Turn-Off Delay Time	$\text{t}_{\text{d(off)}}$			20		
Turn-Off Fall Time	t_f			6		
Total Gate Charge	Q_{g}	$\text{V}_{\text{DS}}=25\text{V}, \text{I}_{\text{D}}=0.22\text{A}, \text{V}_{\text{GS}}=10\text{V}$		1.7	2.4	nC
Gate-Source Charge	Q_{gs}			0.1		
Gate-Drain Charge	Q_{gd}			0.4		
DRAIN-SOURCE DIODE CHARACTERISTICS						
Diode Forward Voltage (Note 3)	V_{SD}	$\text{V}_{\text{GS}}=0\text{V}, \text{I}_{\text{S}}=0.44\text{A}$			1.4	V

NOTES:

1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board, $t \leq 10$ sec.
3. Pulse Test: Pulse Width $\leq 300\mu\text{s}$, Duty Cycle $\leq 2\%$.
4. Guaranteed by design, not subject to production testing.

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

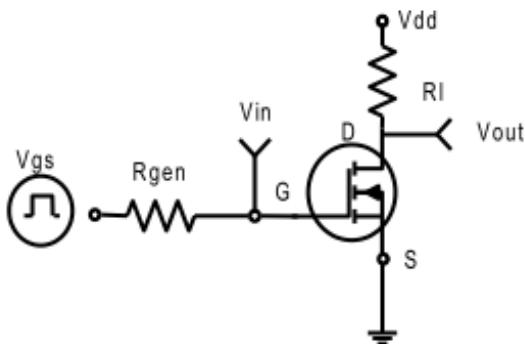


Figure 1:Switching Test Circuit

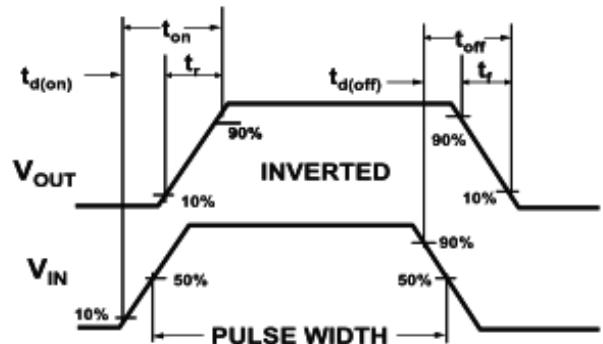


Figure 2:Switching Waveforms

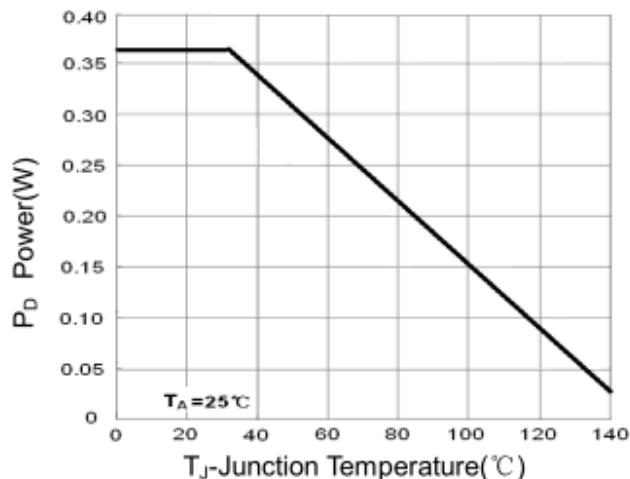


Figure 3 Power Dissipation

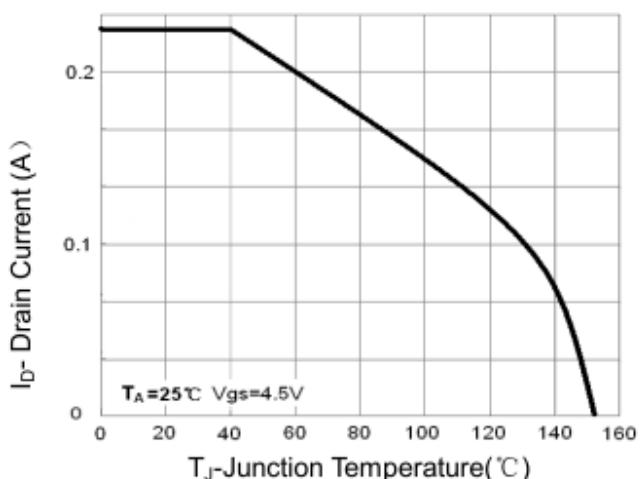


Figure 4 Drain Current

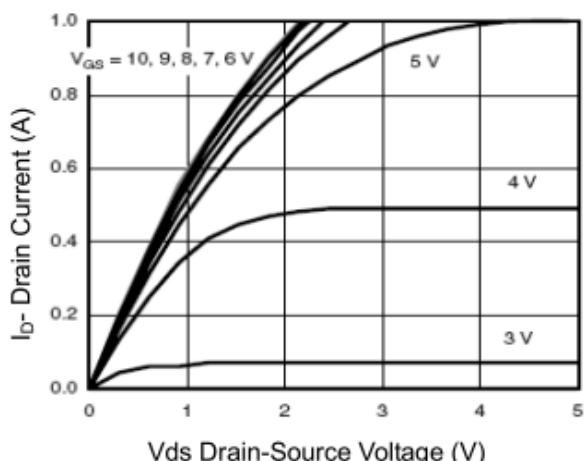


Figure 5 Output CHARACTERISTICS

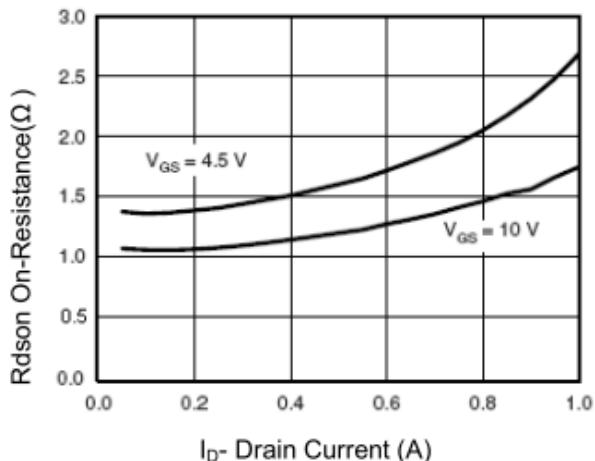


Figure 6 Drain-Source On-Resistance

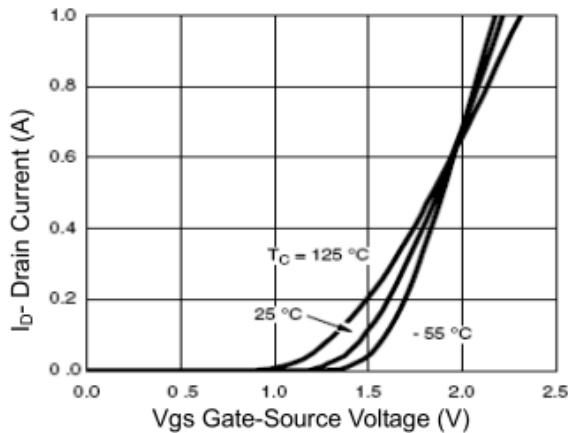


Figure 7 Transfer Characteristics

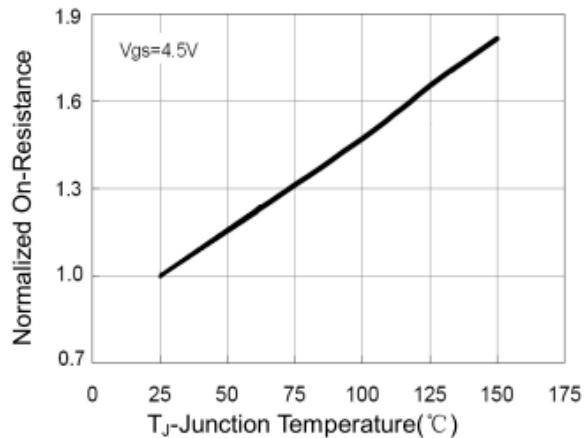


Figure 8 Drain-Source On-Resistance

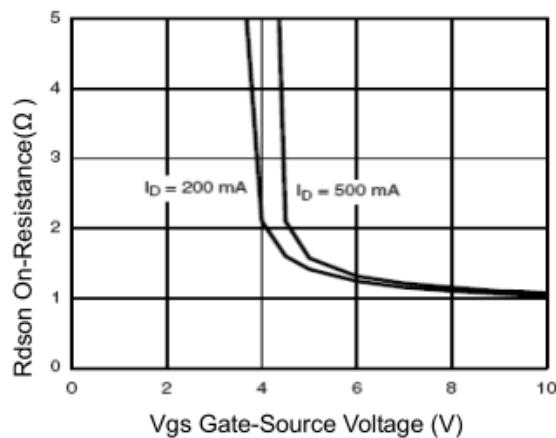


Figure 9 $R_{DS(on)}$ vs V_{GS}

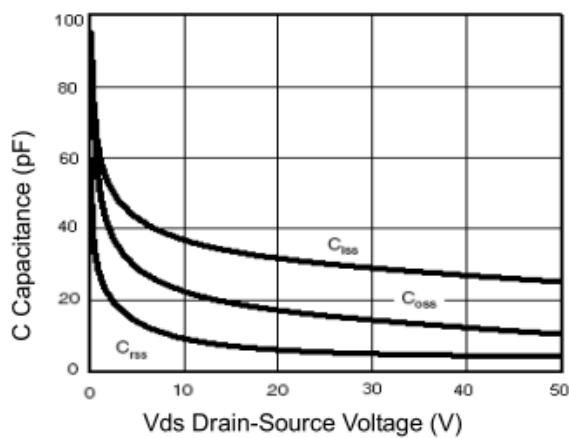


Figure 10 Capacitance vs V_{DS}

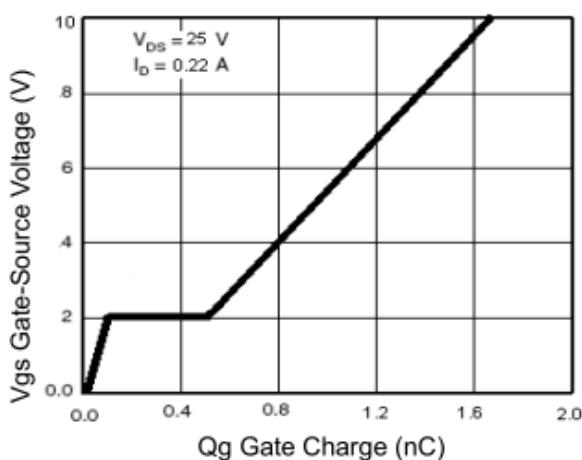


Figure 11 Gate Charge

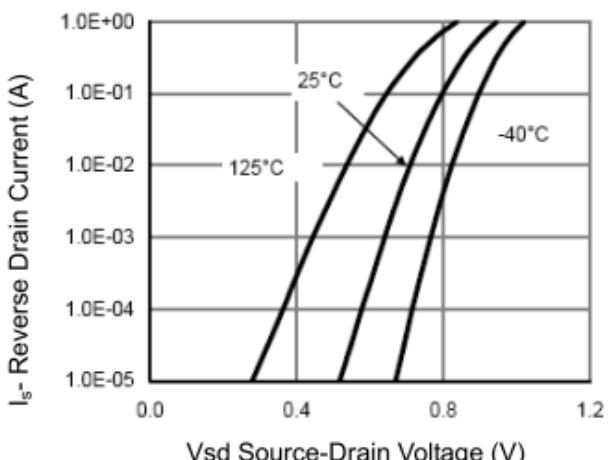


Figure 12 Source-Drain Diode Forward

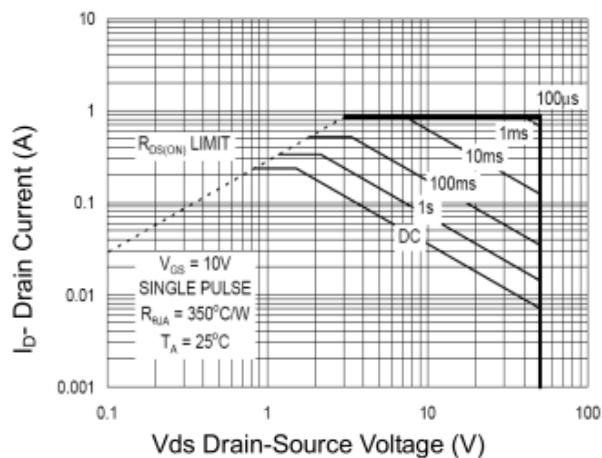


Figure 13 Safe Operation Area

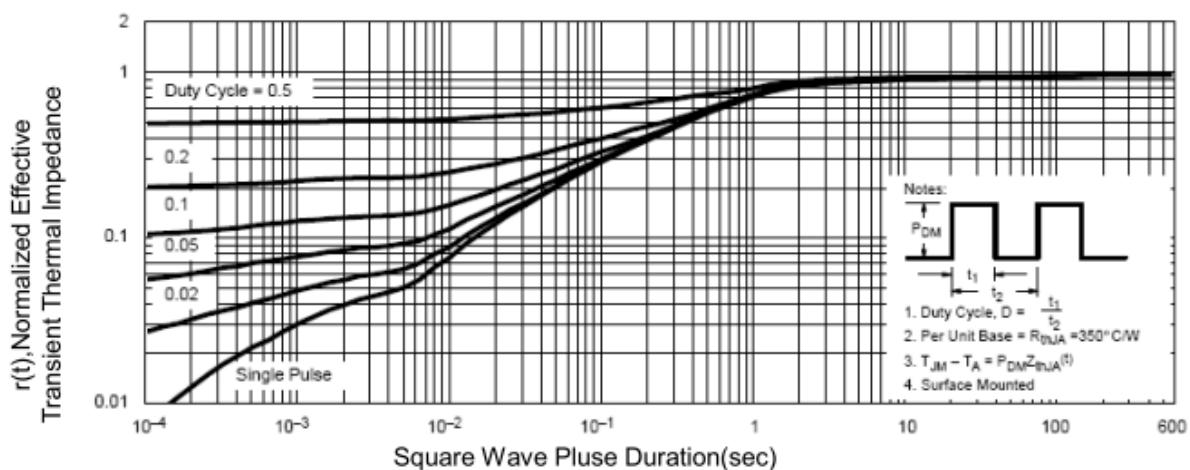
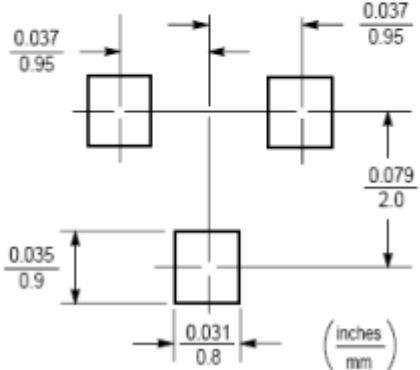
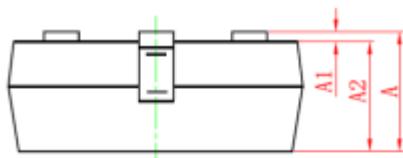
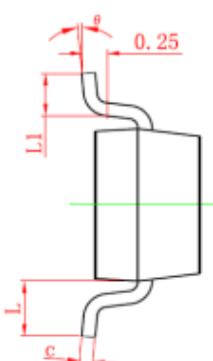
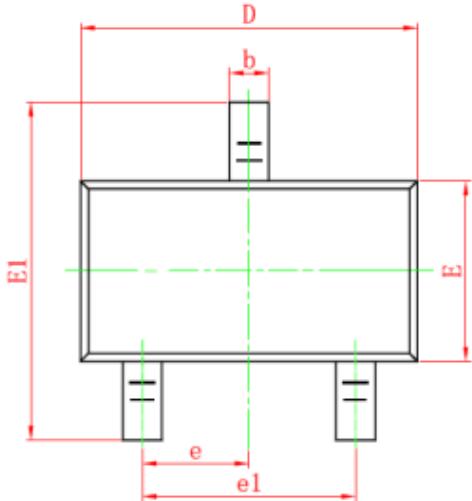


Figure 14 Normalized Maximum Transient Thermal Impedance

Package Information SOT 23

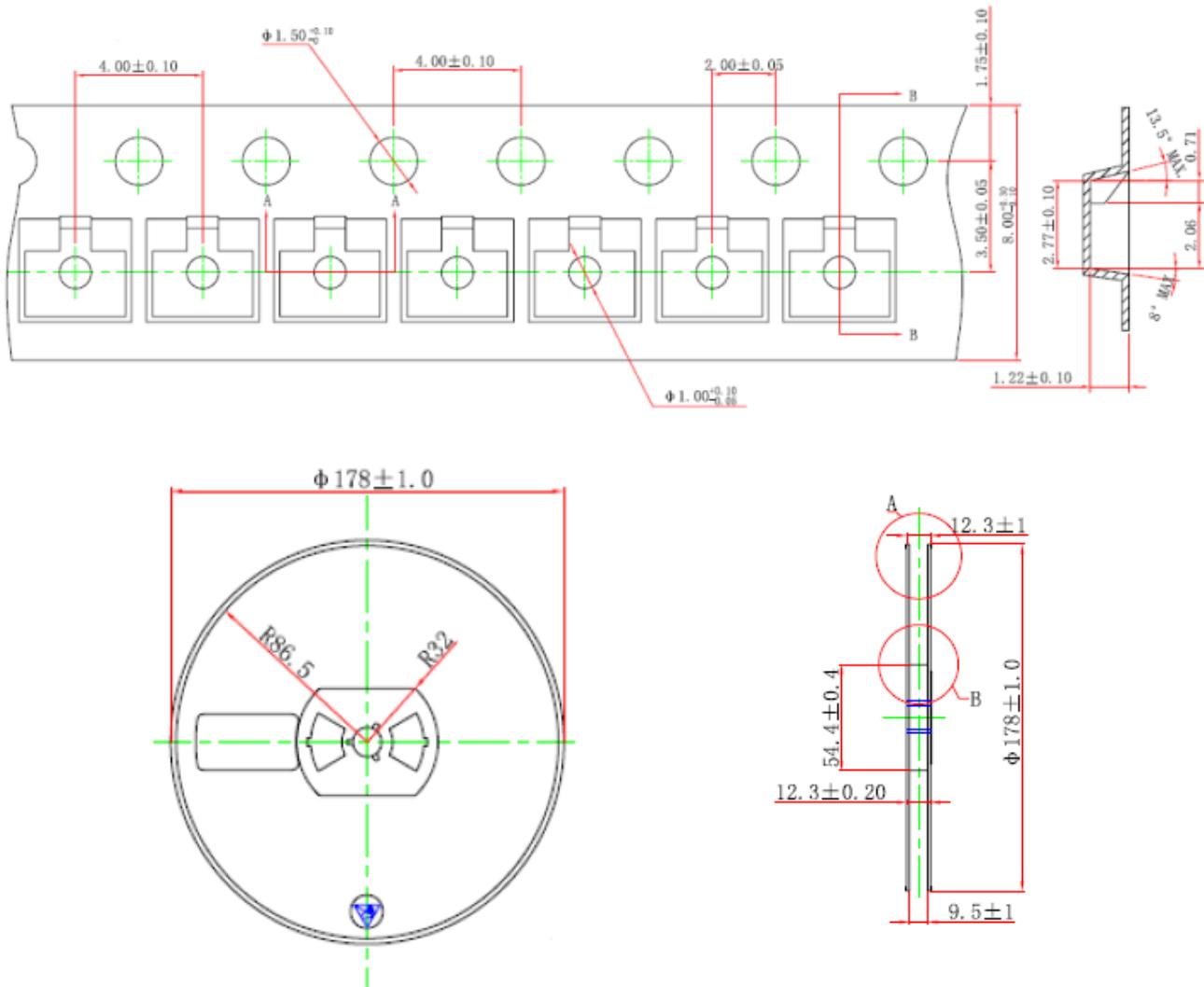


Symbol	Dimensions in Millimeters	
	MIN.	MAX.
A	0.900	1.150
A1	0.000	0.100
A2	0.900	1.050
b	0.300	0.500
c	0.080	0.150
D	2.800	3.000
E	1.200	1.400
E1	2.250	2.550
e	0.950TYP	
e1	1.800	2.000
L	0.550REF	
L1	0.300	0.500
θ	0°	8°

NOTES

1. All dimensions are in millimeters.
2. Tolerance $\pm 0.10\text{mm}$ (4 mil) unless otherwise specified
3. Package body sizes exclude mold flash and gate burrs. Mold flash at the non-lead sides should be less than 5 mils.
4. Dimension L is measured in gauge plane.
5. Controlling dimension is millimeter, converted inch dimensions are not necessarily exact.

SOT 23 Tape and Reel Information



NOTES :

1. All dimensions are in millimeters.
2. 10 Sprocket hole pitch cumulative tolerance $\pm 0.20\text{MAX}$
3. General tolerance ± 0.25